**AMENDMENTS TO THE DRAWINGS:**

The drawings are amended as described below by presenting replacement figures as attached hereto.

In the Office Action at page 2, the Examiner objected to the drawings. In order to overcome these objections, a replacement figure is submitted herewith. In FIG. 6, the primary crystal grain boundaries are shown inclined to a current direction between active channel regions of the thin film transistor at an angle of $-45° \leq \Theta \leq 45°$. Approval of these changes to the drawings is respectfully requested.

Furthermore, FIGS. 2A and 2B also illustrate primary crystal grain boundaries inclined to a current direction between active channel regions of the thin film transistor at an angle of $-45° \leq \Theta \leq 45°$. Accordingly, Applicants assert that the drawings show every feature of the invention and respectfully request that the objection to the drawings be withdrawn.

**IN THE CLAIMS:**

The text of all pending claims, (including withdrawn claims) is set forth below. Cancelled and not entered claims are indicated with claim number and status only. The claims as listed below show added text with underlining and deleted text with ~~strikethrough~~. The status of each claim is indicated with one of (original), (currently amended), (cancelled), (withdrawn), (new), (previously presented), or (not entered).

None of the claims have been amended or cancelled. The following is a list of all claims pending and their current status for the convenience of the Examiner.

1. (Original) A thin film transistor (TFT) comprising a lightly doped drain (LDD) region or offset region, wherein the thin film transistor is formed so that primary crystal grain boundaries of a polysilicon substrate are not positioned in the LDD or offset region.

2. (Original) The thin film transistor according to claim 1, wherein a width of an activation layer including the LDD region or offset region is shorter than a distance between the primary crystal grain boundaries.

3. (Original) The thin film transistor according to claim 1, wherein the polysilicon substrate is formed by a sequential lateral solidification (SLS) method.

4. (Original) The thin film transistor according to claim 1, wherein the thin film transistor is used in an LCD (liquid crystal display) or organic EL (electroluminescent) device.

5. (Original) The thin film transistor according to claim 1, wherein the primary crystal grain boundaries are perpendicular to a current direction between active channel regions of the thin film transistor.

6. (Original) The thin film transistor according to claim 1, wherein the primary crystal grain boundaries are inclined to a current direction between active channel regions of the thin film transistor at an angle of $-45° \leq \Theta \leq 45°$.

7. (Original) A flat panel display device comprising:

a thin film transistor comprising:

an LDD region or offset region,

wherein the thin film transistor is formed so that primary crystal grain boundaries of a polysilicon substrate are not positioned in the LDD or offset region.

8. (Original) The flat panel display device according to claim 7, wherein a width of an activation layer including the LDD region or offset region is shorter than a distance between the primary crystal grain boundaries.

9. (Original) The flat panel display device according to claim 7, wherein the polysilicon substrate is formed by a sequential lateral solidification (SLS) method.

10. (Original) The flat panel display device according to claim 7, wherein the thin film transistor is used in an LCD (liquid crystal display) or organic EL (electroluminescent) device.

11. (Original) The flat panel display device according to claim 7, wherein the primary crystal grain boundaries are perpendicular to a current direction between active channel regions of the thin film transistor.

12. (Original) The flat panel display device according to claim 7, wherein the primary crystal grain boundaries are inclined to a current direction between active channel regions of the thin film transistor at an angle of $-45° \leq \Theta \leq 45°$.